



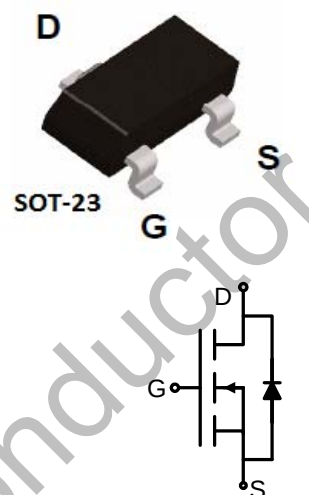
WG2300

20V N-Channel MOSFET

Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 6nC (Typ.).
- ☐ BVDS=20V, ID=6A
- ☐ RDS(on) : 28mΩ (Max) @VG=4.5V, ID=4.5A
- ☐ 100% Avalanche Tested

SOT-23



MARKING:2300

Schematic diagram

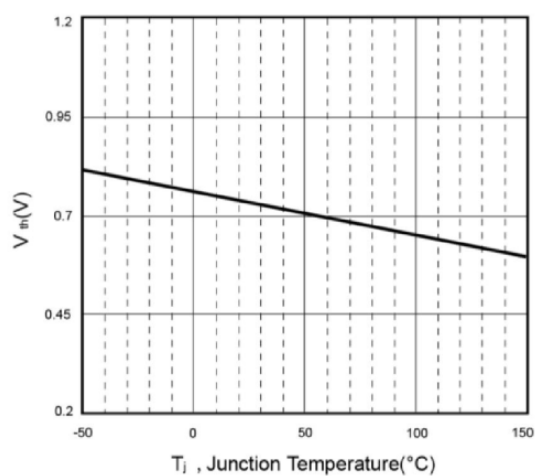
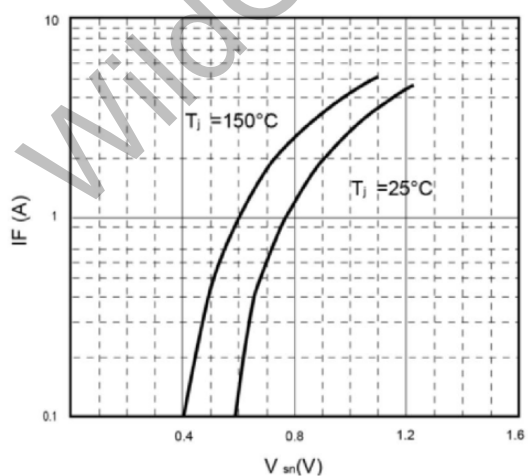
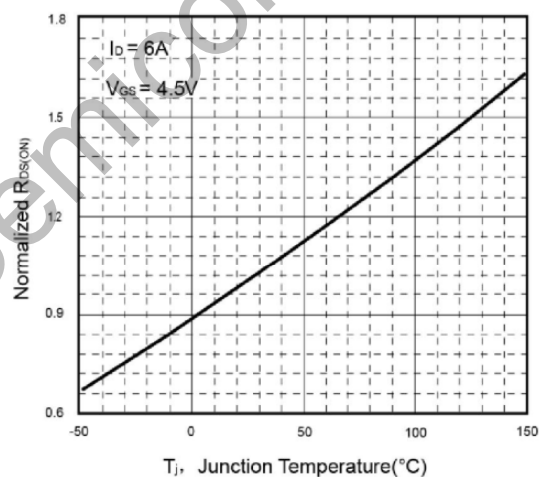
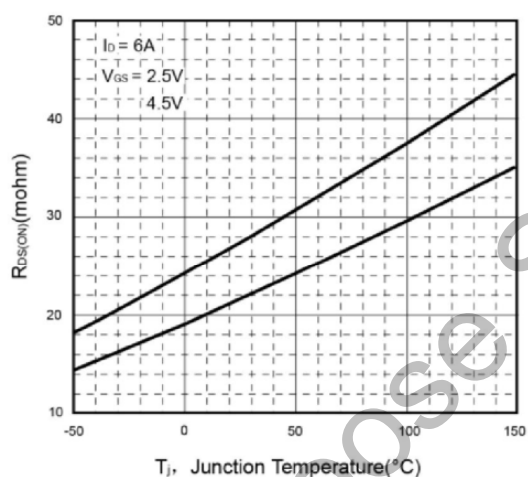
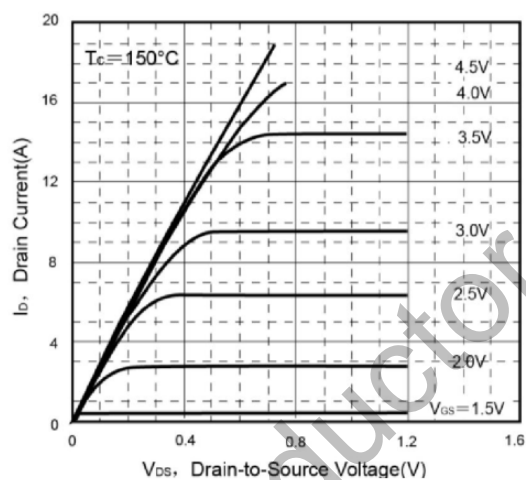
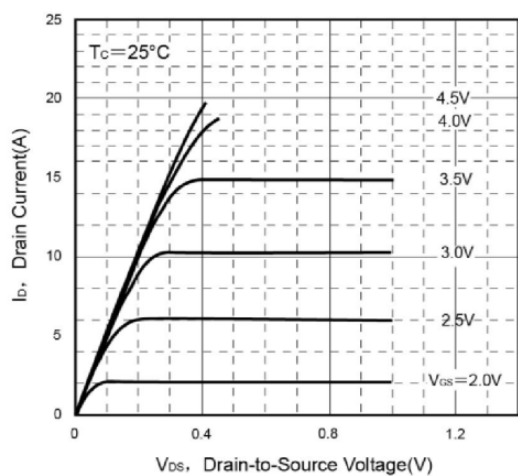
Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	6	A
Drain Current-Pulsed ^(Note 1)	I _{DM}	20	A
Maximum Power Dissipation	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 150	°C

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.65	1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=4.5A$	-	23.6	28	m Ω
		$V_{GS}=2.5V, I_D=3.5A$	-	29.9	38	m Ω
		$V_{GS}=1.8V, I_D=2A$	-	38.5	50	m Ω
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0MHz$	-	247	-	PF
Output Capacitance	C_{oss}		-	34	-	PF
Reverse Transfer Capacitance	C_{rss}		-	19.5	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=10V, R_G=1\ \Omega$ $I_D=1.5A,$	-	6	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=3A,$ $V_{GS}=4.5V$	-	6	-	nC
Gate-Source Charge	Q_{gs}		-	1	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=6A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	6	A

Typical Characteristics



Typical Characteristics (Continued)

